

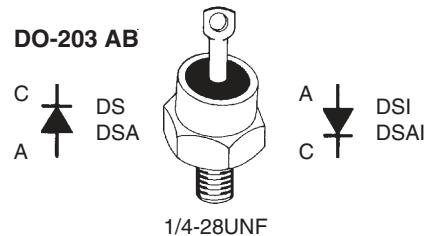
Rectifier Diode

Avalanche Diode

V_{RRM} = 1200-1800 V
I_{F(RMS)} = 80 A
I_{F(AV)M} = 49 A

V _{RSM} V	V _{(BR)min} V	V _{RRM} V	Anode on stud	Cathode on stud
1300	-	1200	DS 35-12A	DSI 35-12A
1300	1300	1200	DSA 35-12A	DSA 35-12A
1700	1750	1600	DSA 35-16A	DSA 35-16A
1900	1950	1800	DSA 35-18A	DSA 35-18A

① Only for Avalanche Diodes



A = Anode C = Cathode

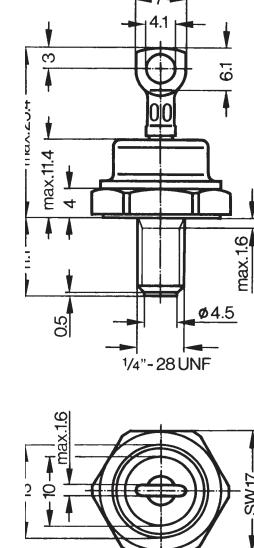
Symbol	Test Conditions	Maximum Ratings		
I _{F(RMS)}	T _{VJ} = T _{VJM}	80	A	
I _{F(AV)M}	T _{case} = 100°C; 180° sine	49	A	
P _{RSM}	DSA(I) types, T _{VJ} = T _{VJM} , t _p = 10 µs	11	kW	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	650	A	
	V _R = 0 t = 8.3 ms (60 Hz), sine	690	A	
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	600	A	
	V _R = 0 t = 8.3 ms (60 Hz), sine	640	A	
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	2100	A ² s	
	V _R = 0 t = 8.3 ms (60 Hz), sine	2000	A ² s	
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	1800	A ² s	
	V _R = 0 t = 8.3 ms (60 Hz), sine	1700	A ² s	
T _{VJ}		-40...+180	°C	
T _{VJM}		180	°C	
T _{stg}		-40...+180	°C	
M _d	Mounting torque	4.5-5.5 40-49	Nm lb.in.	
Weight		15	g	

Symbol	Test Conditions	Characteristic Values		
I _R	T _{VJ} = T _{VJM} ; V _R = V _{RRM}	≤ 4	mA	
V _F	I _F = 150 A; T _{VJ} = 25°C	≤ 1.55	V	
V _{T0}	For power-loss calculations only	0.85	V	
r _T	T _{VJ} = T _{VJM}	4.5	mΩ	
R _{thJC}	DC current	1.05	K/W	
R _{thJH}	DC current	1.25	K/W	
d _S	Creepage distance on surface	4.05	mm	
d _A	Strike distance through air	3.9	mm	
a	Max. allowable acceleration	100	m/s ²	

Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

Dimensions in mm (1 mm = 0.0394")



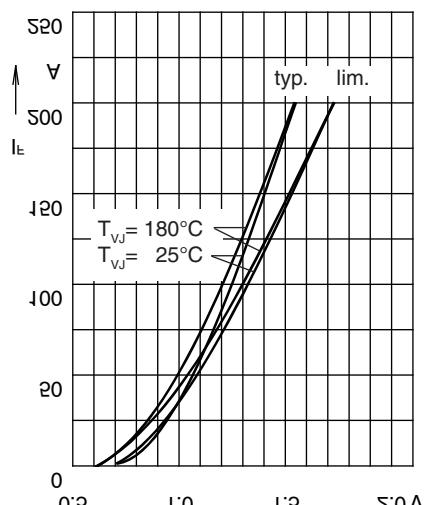


Fig. 1 Forward characteristics

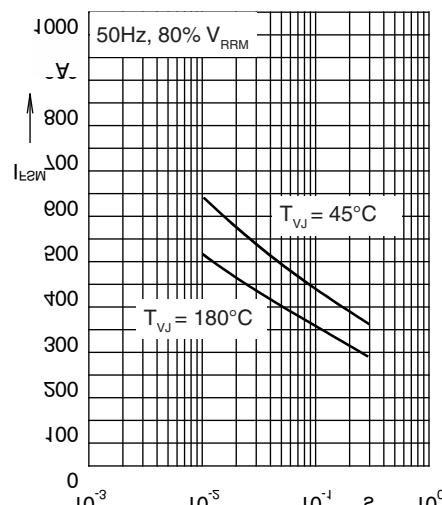
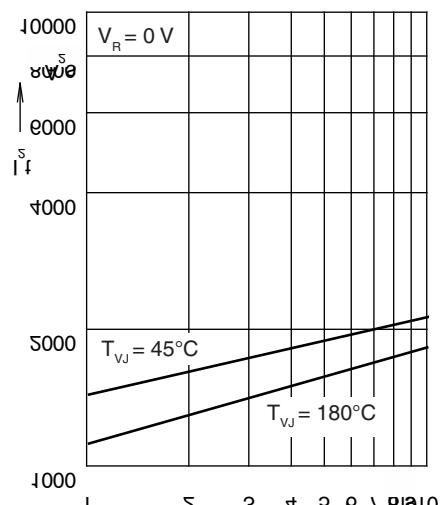
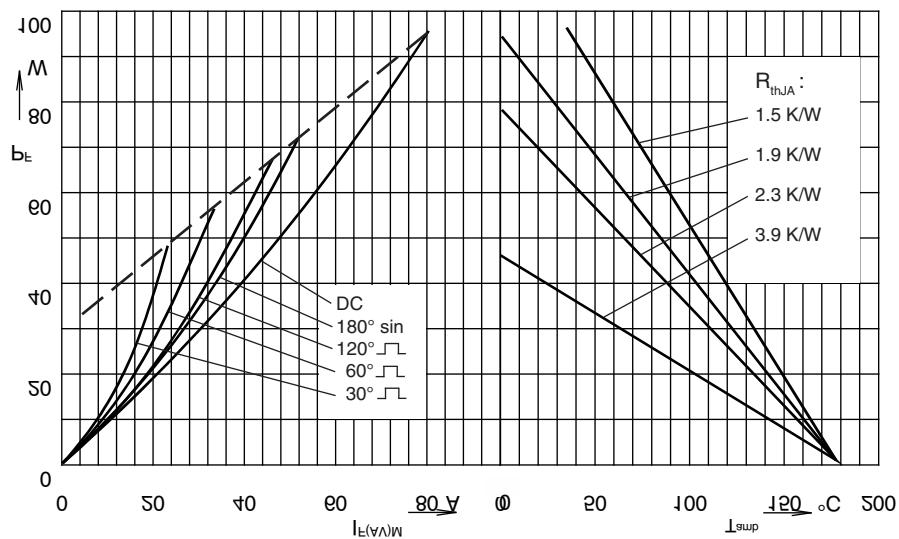

 Fig. 2 Surge overload current
 I_{FSM} : crest value, t : duration

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Power dissipation versus forward current and ambient temperature

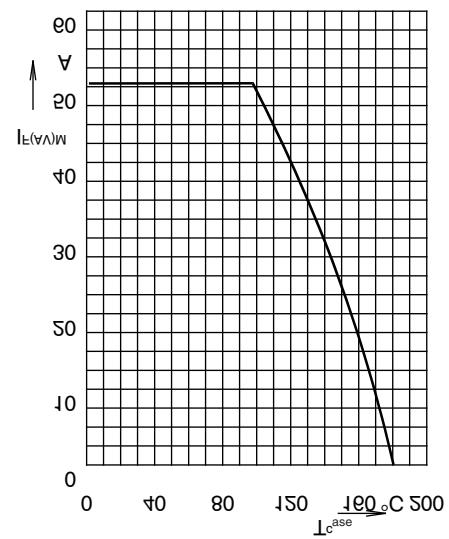


Fig. 5 Max. forward current at case temperature 180° sine

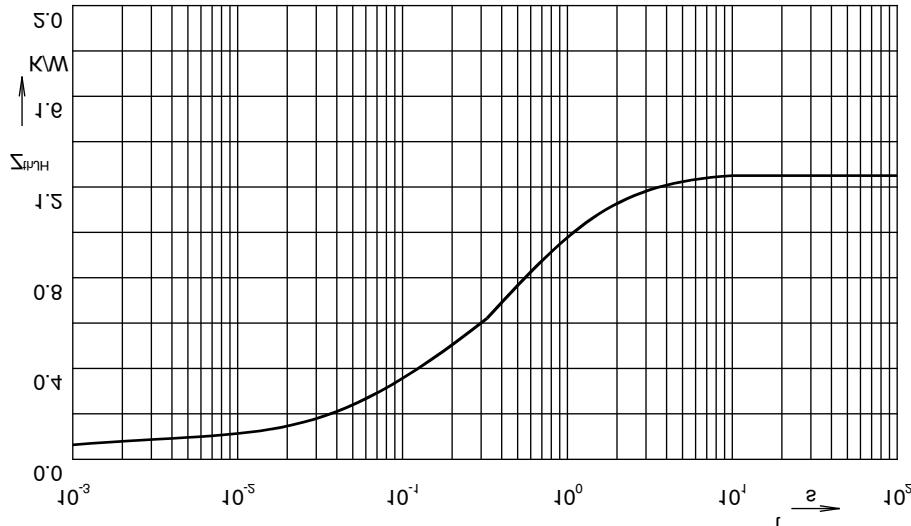


Fig. 6 Transient thermal impedance junction to heatsink

 R_{thjH} for various conduction angles d:

d	R_{thjH} (K/W)
DC	1.25
180°	1.37
120°	1.47
60°	1.74
30°	2.08

 Constants for Z_{thjH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.10	0.0012
2	0.25	0.1181
3	0.70	0.6540
4	0.20	2.0